

## Supplemental Material

In Figure 7 we monitored the DOS transition in the 3d period, and in Figure 8 total DOS at  $E_F$  was given for both 3d and 4d periods, but information for 5d period was not supplied because there are only three mechanically stable 5d pernitrides,  $\text{HfN}_2$ ,  $\text{IrN}_2$  and  $\text{PtN}_2$ . We provide below in Figure A, the DOS of the adjacent  $\text{IrN}_2$ ,  $\text{PtN}_2$  and  $\text{AuN}_2$  (unstable) in 5d period. We can see the reason why  $\text{PtN}_2$  is a semiconductor but neither  $\text{IrN}_2$  nor  $\text{AuN}_2$ . It is the left shift and width-narrowing behavior of DOS, placing a gap of states at the  $E_F$  of  $\text{PtN}_2$ .

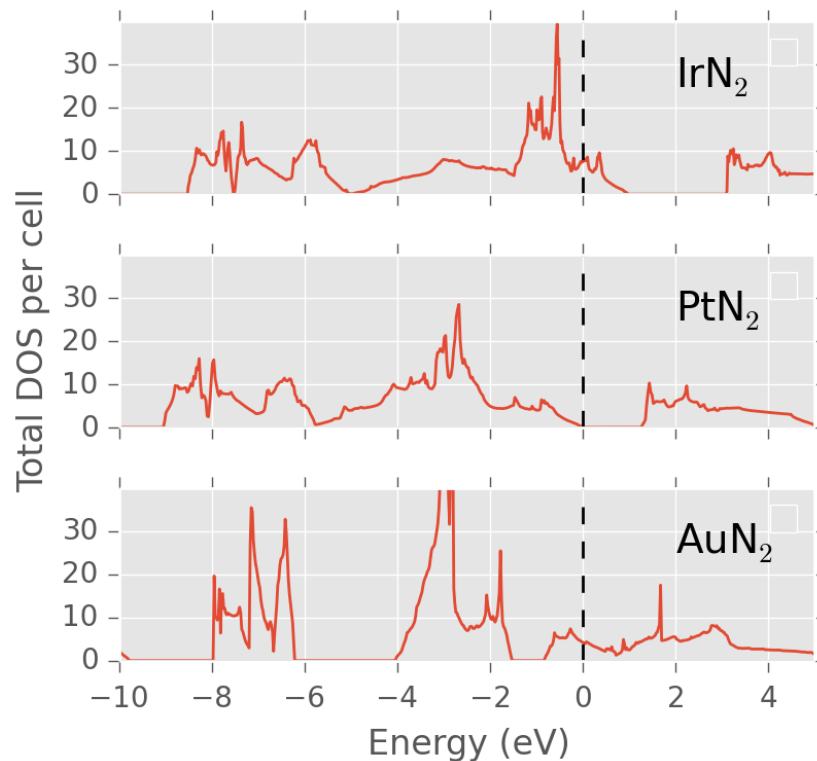


Figure A. Total density of states of pyrite-type  $\text{IrN}_2$ ,  $\text{PtN}_2$  and  $\text{AuN}_2$ .

Looking at the data by group number, in Figure 8, we see Group 10 metal pernitrides  $\text{NiN}_2$  (3d),  $\text{PdN}_2$  (4d) and  $\text{PtN}_2$  (5d) having small values of total DOS at  $E_F$ . In Figure 7 there is a DOS plot for  $\text{NiN}_2$  and there is a small notch between the two peaks at  $E_F$ ; there is no gap, so it might not be appropriate to call it a semiconductor. But if we look at the cases of  $\text{PdN}_2$  or  $\text{PtN}_2$  in Figure B provided below, our calculations show that they are semiconductors with band gaps. The same situation goes for Group 4 pernitrides  $\text{TiN}_2$ ,  $\text{ZrN}_2$  and  $\text{HfN}_2$  in Figure C, where  $E_F$  of  $\text{TiN}_2$  lies in the valley between two peaks, but both  $\text{ZrN}_2$  and  $\text{HfN}_2$  are semiconductors.

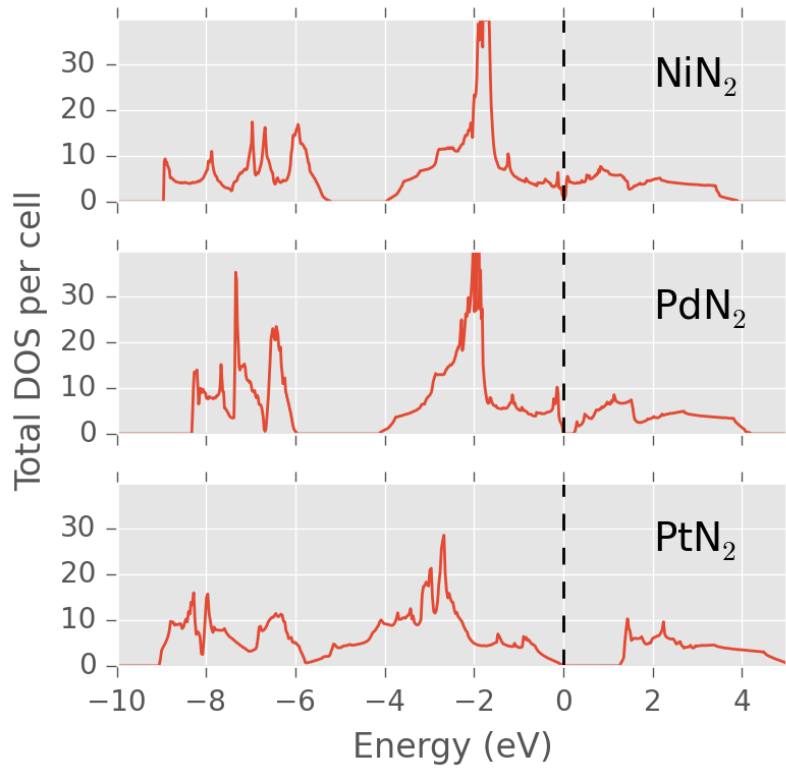


Figure B. Total density of states of pyrite-type  $\text{NiN}_2$ ,  $\text{PdN}_2$  and  $\text{PtN}_2$ .

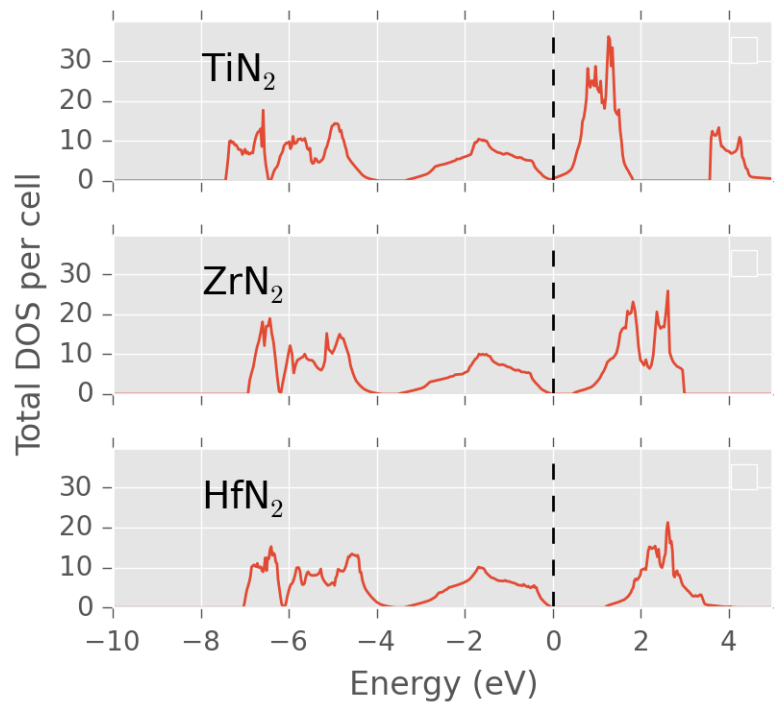


Figure C. Total density of states of pyrite-type  $\text{TiN}_2$ ,  $\text{ZrN}_2$  and  $\text{HfN}_2$ .

Summarizing the above, as the transition metal choice moves in the periodic table, the pernitride demonstrates metallic or non-metallic behavior, depending on the relative

position of  $E_F$  in DOS. This formation of the electronic band gap for a specific compound such as  $PtN_2$  within the class of all structurally isomorphic transition metal pnitrides is determined by the correct appearance of  $E_F$  within the gaps between two energy bands available for filling electrons. These bands get filled as one adds one electron as the group number of the transition metal atom increases by one. The precise location of  $E_F$  on the energy x-axis of a figure like Figure 7 can only be obtained by detailed fully quantum mechanical computations as we have performed. Semiconductors can show up in various group numbers, and certainly can be analyzed along with metallic phases. The rules we are aiming to formulate apply to both.